

# 2N3903, 2N3904

## General Purpose Transistors

### NPN Silicon

#### Features

- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	40	Vdc
Collector - Base Voltage	$V_{CBO}$	60	Vdc
Emitter - Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	$I_C$	200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

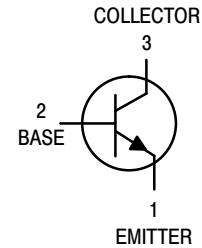
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates Data in addition to JEDEC Requirements.

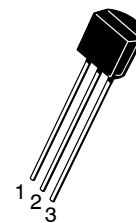


ON Semiconductor®

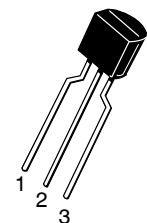
<http://onsemi.com>



TO-92  
CASE 29  
STYLE 1

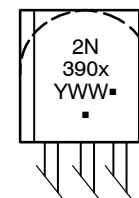


STRAIGHT LEAD  
BULK PACK



BENT LEAD  
TAPE & REEL  
AMMO PACK

#### MARKING DIAGRAMS



- x = 3 or 4
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2N3903, 2N3904

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector – Emitter Breakdown Voltage (Note 2) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	40	–	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	–	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	–	Vdc
Base Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>BL</sub>	–	50	nAdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>CEX</sub>	–	50	nAdc

### ON CHARACTERISTICS

DC Current Gain (Note 2) (I <sub>C</sub> = 0.1 mAdc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 1.0 Vdc)	2N3903	h <sub>FE</sub>	20	–	–
	2N3904		40	–	–
	2N3903		35	–	–
	2N3904		70	–	–
	2N3903		50	150	–
	2N3904		100	300	–
	2N3903		30	–	–
	2N3904		60	–	–
Collector – Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)		V <sub>CE(sat)</sub>	–	0.2	Vdc
			–	0.3	
Base – Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)		V <sub>BE(sat)</sub>	0.65	0.85	Vdc
			–	0.95	

### SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)	2N3903	f <sub>T</sub>	250	–	MHz
	2N3904		300	–	
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	–	4.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ibo</sub>	–	8.0	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3903	h <sub>ie</sub>	1.0	8.0	k Ω
	2N3904		1.0	10	
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3903	h <sub>re</sub>	0.1	5.0	X 10 <sup>-4</sup>
	2N3904		0.5	8.0	
Small-Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3903	h <sub>fe</sub>	50	200	–
	2N3904		100	400	
Output Admittance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)		h <sub>oe</sub>	1.0	40	μmhos
Noise Figure (I <sub>C</sub> = 100 μAdc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 k Ω, f = 1.0 kHz)	2N3903	NF	–	6.0	dB
	2N3904		–	5.0	

### SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = 0.5 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)		t <sub>d</sub>	–	35	ns
Rise Time			t <sub>r</sub>	–	35	ns
Storage Time	(V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mAdc)	2N3903 2N3904	t <sub>s</sub>	–	175 200	ns
Fall Time			t <sub>f</sub>	–	50	ns

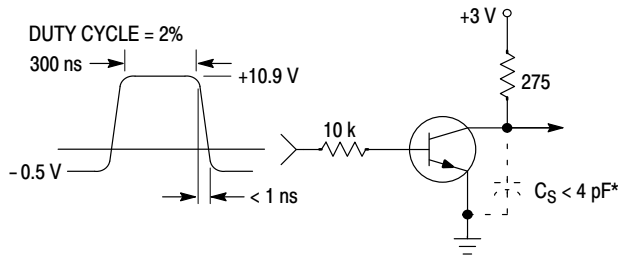
2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

## 2N3903, 2N3904

### ORDERING INFORMATION

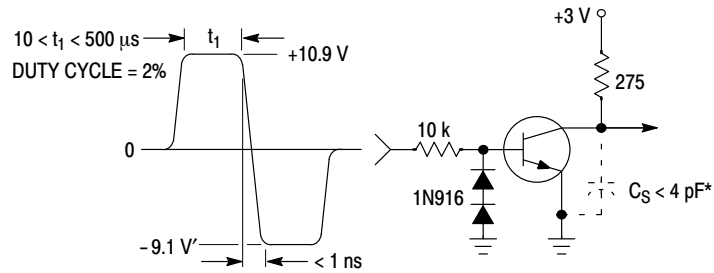
Device	Package	Shipping†
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92	2000 / Ammo Pack
2N3904ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



\* Total shunt capacitance of test jig and connectors

**Figure 1. Delay and Rise Time Equivalent Test Circuit**



\* Total shunt capacitance of test jig and connectors

**Figure 2. Storage and Fall Time Equivalent Test Circuit**

TYPICAL TRANSIENT CHARACTERISTICS

—  $T_J = 25^\circ\text{C}$   
 - - -  $T_J = 125^\circ\text{C}$

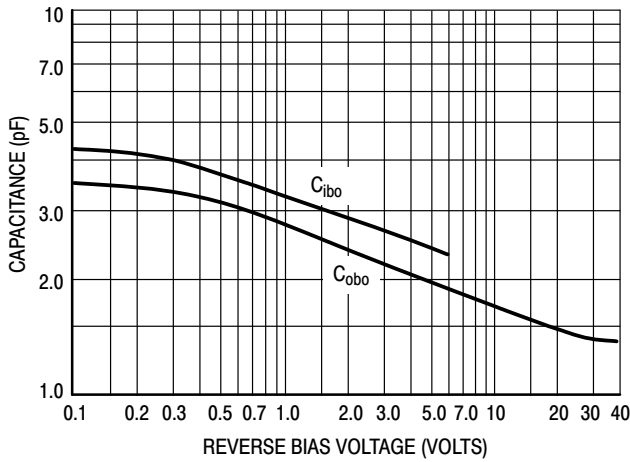


Figure 3. Capacitance

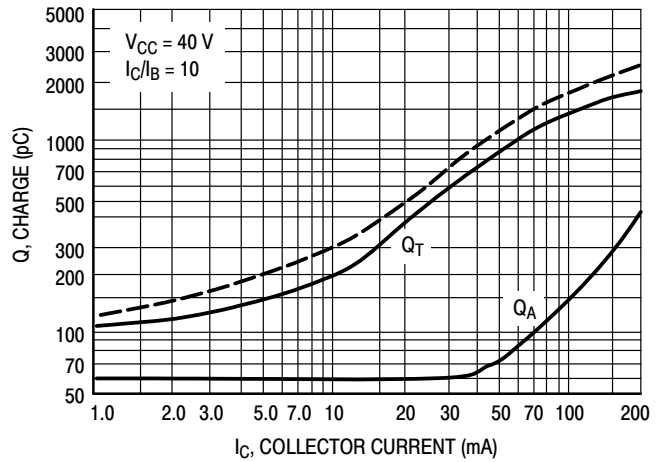


Figure 4. Charge Data

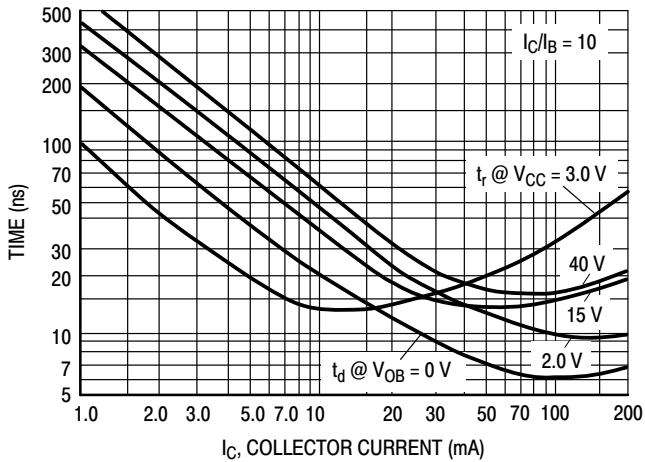


Figure 5. Turn-On Time

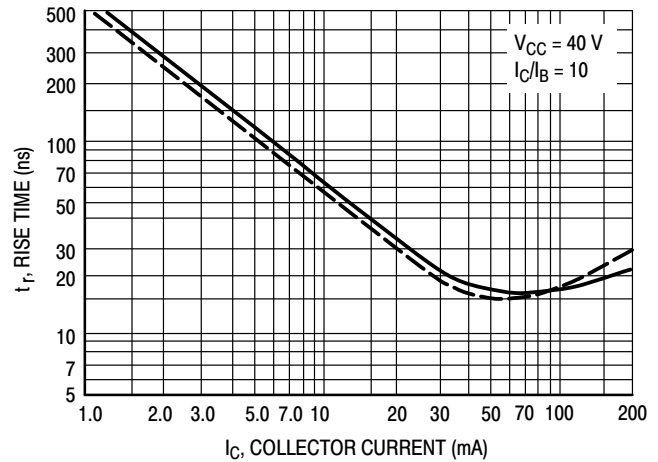


Figure 6. Rise Time

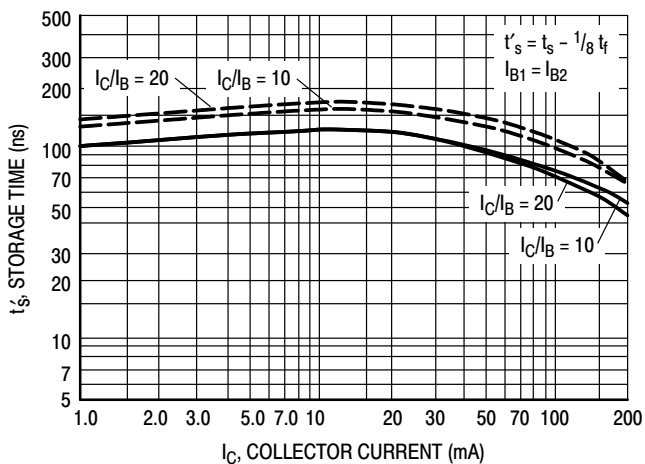


Figure 7. Storage Time

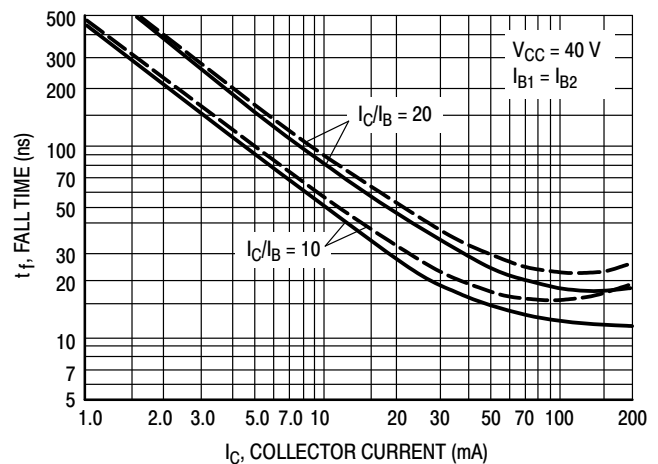


Figure 8. Fall Time

# 2N3903, 2N3904

## TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

( $V_{CE} = 5.0$  Vdc,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)

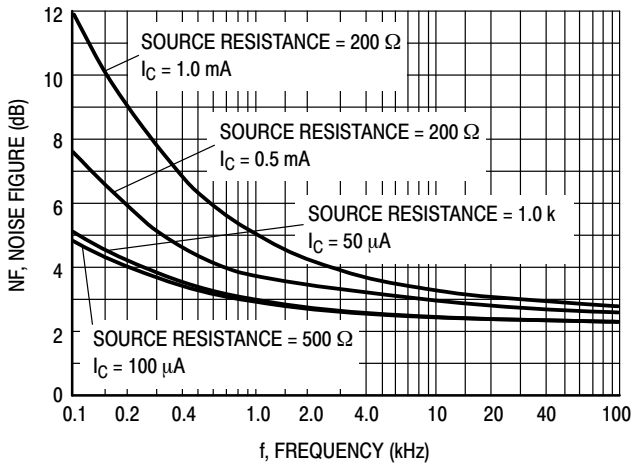


Figure 9.

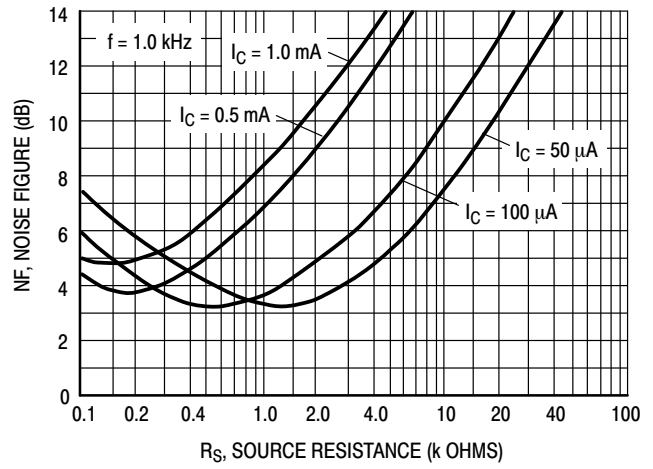


Figure 10.

## h PARAMETERS

( $V_{CE} = 10$  Vdc,  $f = 1.0$  kHz,  $T_A = 25^\circ\text{C}$ )

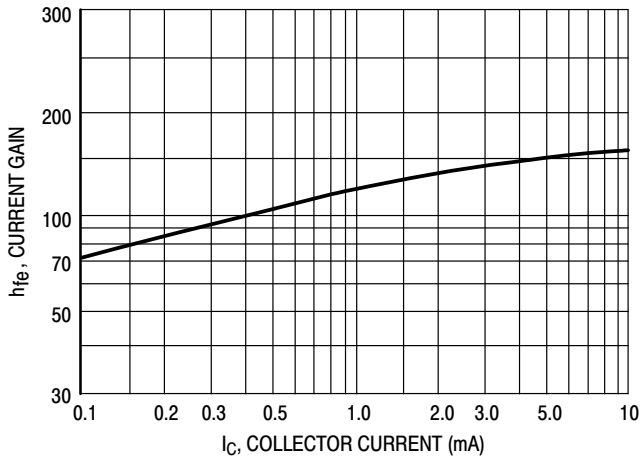


Figure 11. Current Gain

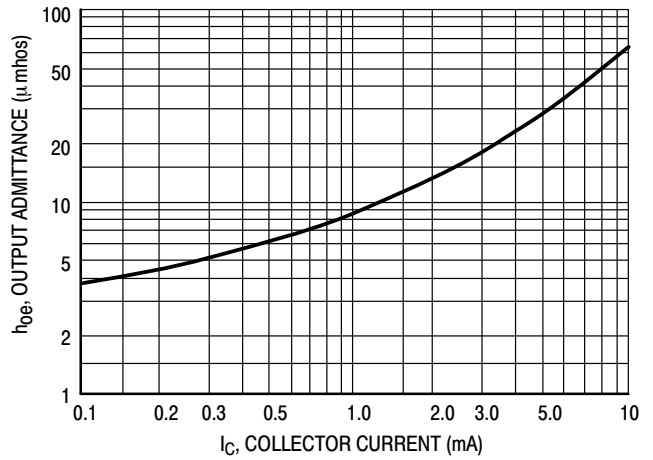


Figure 12. Output Admittance

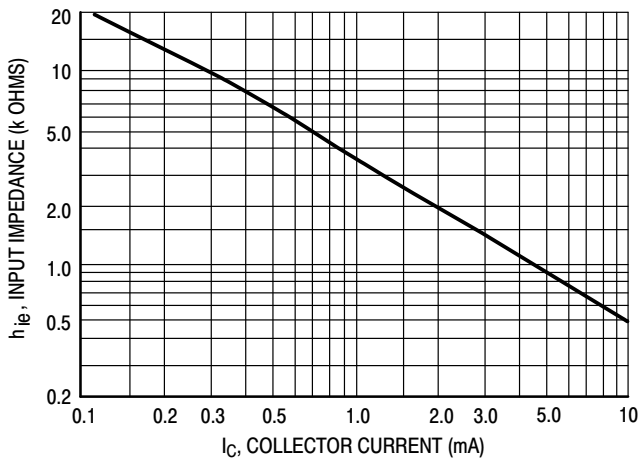


Figure 13. Input Impedance

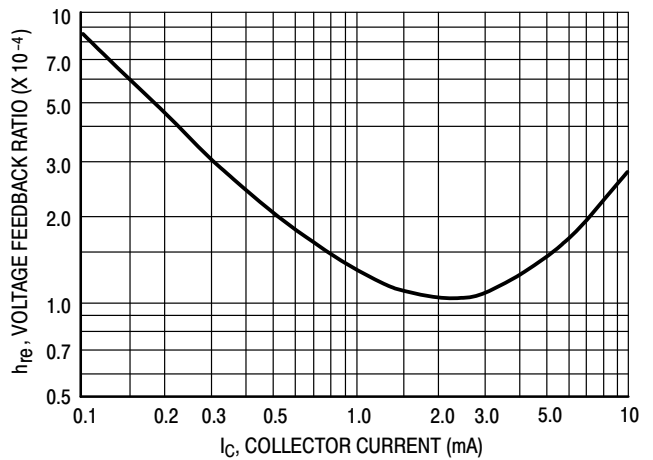


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

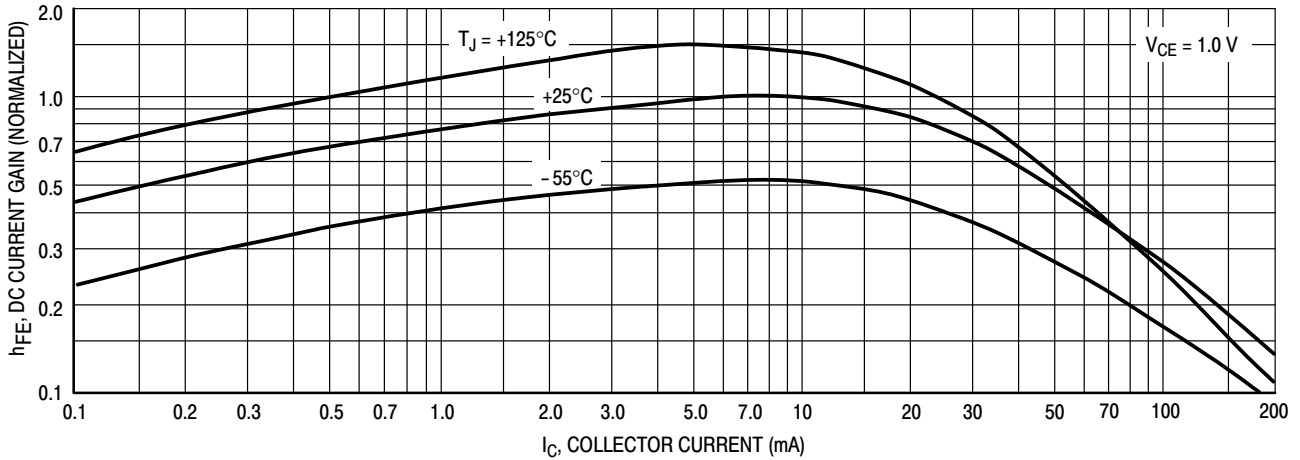


Figure 15. DC Current Gain

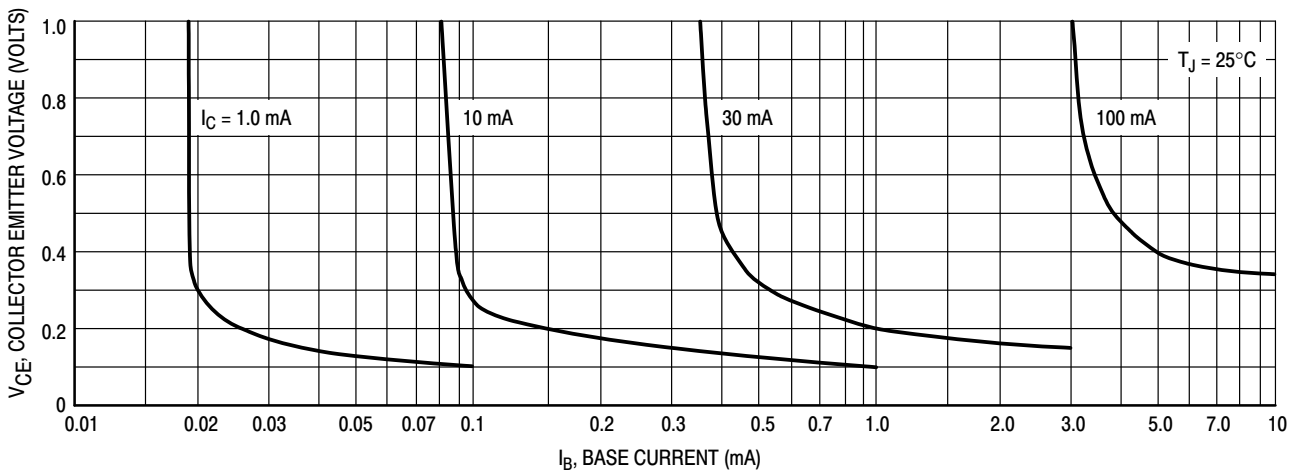


Figure 16. Collector Saturation Region

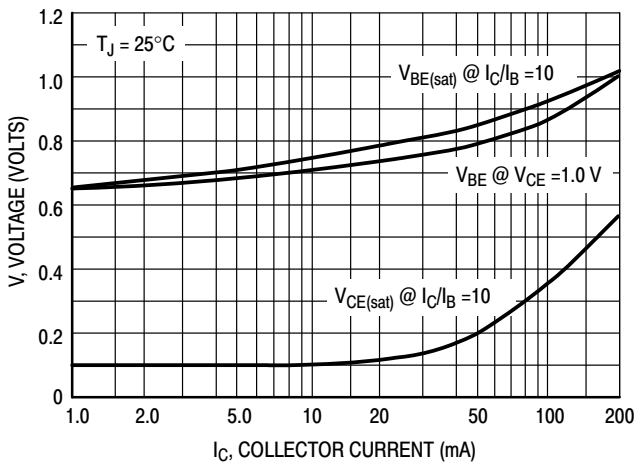


Figure 17. "ON" Voltages

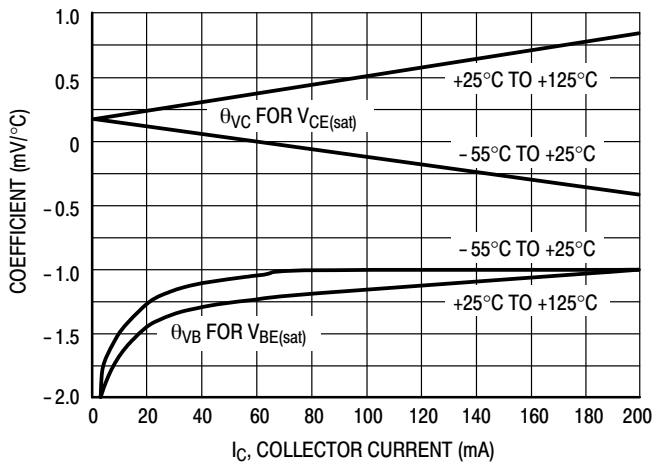


Figure 18. Temperature Coefficients

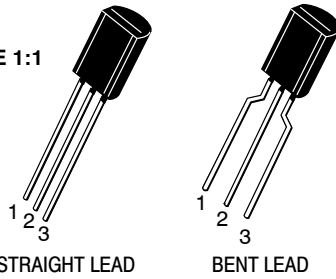
# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®

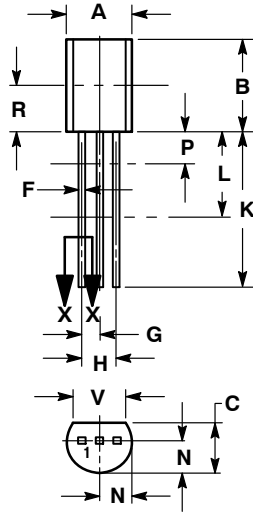


SCALE 1:1



TO-92 (TO-226) 1 WATT  
CASE 29-10  
ISSUE A

DATE 08 MAY 2012

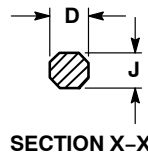


STRAIGHT LEAD

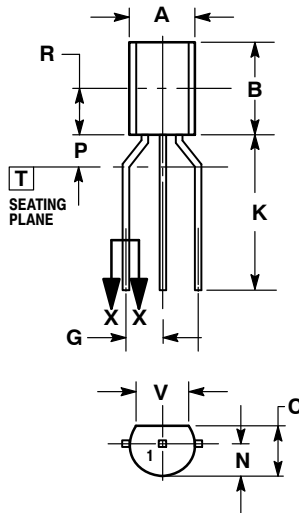
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---



SECTION X-X

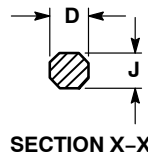


BENT LEAD

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---



SECTION X-X

STYLES ON PAGE 2

DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-92 (TO-226) 1 WATT	PAGE 1 OF 2

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**TO-92 (TO-226) 1 WATT  
CASE 29-10  
ISSUE A**

DATE 08 MAY 2012

STYLE 1:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 2:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 5:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 6:  
PIN 1. GATE  
2. SOURCE & SUBSTRATE  
3. DRAIN

STYLE 7:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 8:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE & SUBSTRATE

STYLE 9:  
PIN 1. BASE 1  
2. EMITTER  
3. BASE 2

STYLE 10:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE & ANODE  
3. CATHODE

STYLE 12:  
PIN 1. MAIN TERMINAL 1  
2. GATE  
3. MAIN TERMINAL 2

STYLE 13:  
PIN 1. ANODE 1  
2. GATE  
3. CATHODE 2

STYLE 14:  
PIN 1. EMITTER  
2. COLLECTOR  
3. BASE

STYLE 15:  
PIN 1. ANODE 1  
2. CATHODE  
3. ANODE 2

STYLE 16:  
PIN 1. ANODE  
2. GATE  
3. CATHODE

STYLE 17:  
PIN 1. COLLECTOR  
2. BASE  
3. EMITTER

STYLE 18:  
PIN 1. ANODE  
2. CATHODE  
3. NOT CONNECTED

STYLE 19:  
PIN 1. GATE  
2. ANODE  
3. CATHODE

STYLE 20:  
PIN 1. NOT CONNECTED  
2. CATHODE  
3. ANODE

STYLE 21:  
PIN 1. COLLECTOR  
2. EMITTER  
3. BASE

STYLE 22:  
PIN 1. SOURCE  
2. GATE  
3. DRAIN

STYLE 23:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 24:  
PIN 1. EMITTER  
2. COLLECTOR/ANODE  
3. CATHODE

STYLE 25:  
PIN 1. MT 1  
2. GATE  
3. MT 2

STYLE 26:  
PIN 1. V<sub>CC</sub>  
2. GROUND 2  
3. OUTPUT

STYLE 27:  
PIN 1. MT  
2. SUBSTRATE  
3. MT

STYLE 28:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 29:  
PIN 1. NOT CONNECTED  
2. ANODE  
3. CATHODE

STYLE 30:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE

STYLE 31:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE


STYLE 32:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER

STYLE 33:  
PIN 1. RETURN  
2. INPUT  
3. OUTPUT

STYLE 34:  
PIN 1. INPUT  
2. GROUND  
3. LOGIC

STYLE 35:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER

<b>DOCUMENT NUMBER:</b>	<b>98AON52857E</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>TO-92 (TO-226) 1 WATT</b>	<b>PAGE 2 OF 2</b>

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.



ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

North American Technical Support:  
Voice Mail: 1 800-282-9855 Toll Free USA/Canada  
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative